CTLTVS12

SURFACE MOUNT SILICON TRANSIENT VOLTAGE SUPPRESSOR

TLP™ Tiny Leadless Package

Top View Bottom View

TLM2D3D6 CASE

APPLICATIONS:
- PDAs
- Memory Card Ports
- Cellular Phones
- Instrumentation

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CTLTVS12 is a low leakage, fast response TVS packaged in an ultra small, ultra low profile surface mount package. This device is designed to protect sensitive equipment against ESD damage.

MARKING CODE: O

FEATURES:
- Ultra Small, Ultra Low Profile 0.3mm x 0.6mm x 0.3mm TLP™ Leadless Surface Mount package
- Low Capacitance
- Low Leakage Current
- ESD Protection IEC 61000-4-2:
  Air Discharge - 30kV
  Contact Discharge - 30kV

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Peak Power Dissipation (8x20μs)	P_{PK}	35	W
ESD Voltage	V_{ESD}	30	kV
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C) V_F=1.0V MAX @ I_F=10mA

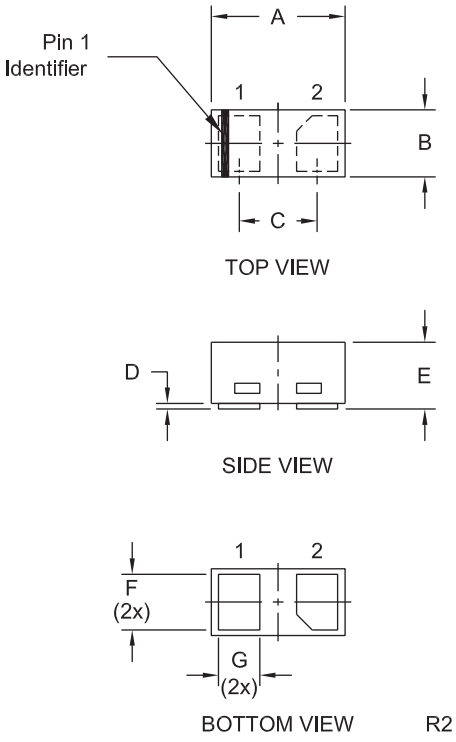
Maximum Reverse Stand-off Voltage V_{RWM}	Breakdown Voltage V_{BR} @ I_T			Test Current I_T	Maximum Reverse Leakage Current I_R @ V_{RWM}	Maximum Clamping Voltage V_C @ I_{PP}	Peak Pulse Current I_{PP}	Typical Capacitance @ 0V Bias	Typical Capacitance @ 9V Bias
V	MIN V	NOM V	MAX V	mA	μA	V	A	pF	pF
9.0	10	12	14	5.0	1.0	18	1.8	14	5.0

R1 (26-January 2012)

CTLTVS12

SURFACE MOUNT SILICON TRANSIENT VOLTAGE SUPPRESSOR

TLM2D3D6 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.022	0.026	0.55	0.65
B	0.010	0.014	0.25	0.35
C	0.014		0.35	
D	0.000	0.002	0.00	0.05
E	0.011	0.013	0.28	0.32
F	0.008	0.012	0.20	0.30
G	0.005	0.009	0.13	0.24

TLM2D3D6 (REV: R2)

LEAD CODE:
1) Cathode
2) Anode

MARKING CODE: O